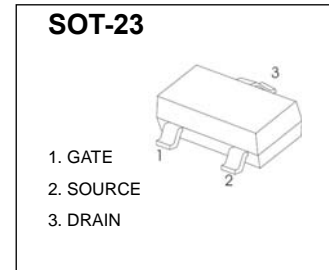
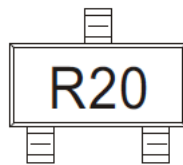
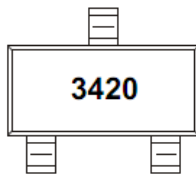


3420 N-Channel Enhancement Mode Field Effect Transistor

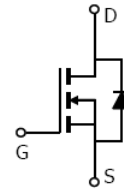
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	24mΩ@10V	6A
	27mΩ@4.5V	
	42mΩ@2.5V	
	74mΩ@1.8V	



MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55 ~ +150	$^\circ\text{C}$

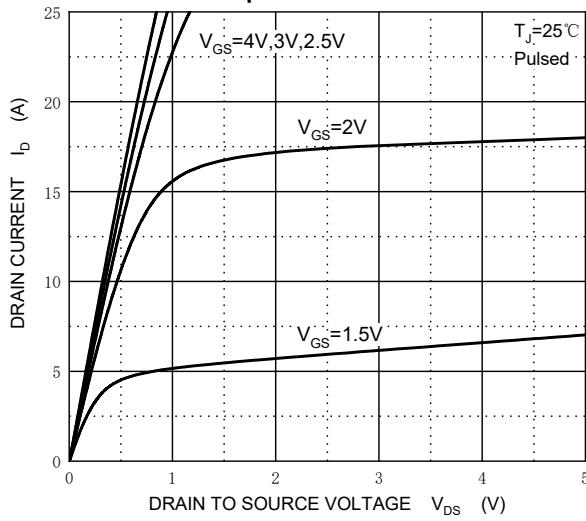
$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V, T_J = 25\text{ }^\circ\text{C}$			1	μA
		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125\text{ }^\circ\text{C}$			1	mA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
On characteristics						
Drain-source on-resistance ^②	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 6A$		19	24	m Ω
		$V_{GS} = 4.5V, I_D = 5A$		22	27	m Ω
		$V_{GS} = 2.5V, I_D = 4A$		27	42	m Ω
		$V_{GS} = 1.8V, I_D = 2A$		38	74	m Ω
Forward transconductance	g_{FS}	$V_{DS} = 5V, I_D = 3.8A$	4			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.7	1.0	V
Dynamic Characteristics ^③						
Input capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		630		pF
Output capacitance	C_{oss}			164		pF
Reverse transfer capacitance	C_{rss}			137		pF
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.5		Ω
Switching Characteristics ^③						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V,$ $R_L = 2.7\Omega, R_{GEN} = 3\Omega$		5.5		ns
Turn-on rise time	t_r			14		ns
Turn-off delay time	$t_{d(off)}$			29		ns
Turn-off fall time	t_f			10.2		ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$		8.8		nC
Gate-Source Charge	Q_{gs}			1		nC
Gate-Drain Charge	Q_{gd}			3.7		nC
Drain-source diode characteristics and maximum ratings						
Diode forward voltage ^②	V_{SD}	$I_S = 1A, V_{GS} = 0V$		0.75	1	V
Continuous drain-source diode forward current	I_S				6	A
Pulsed drain-source diode forward current ^①	I_{SM}				25	A

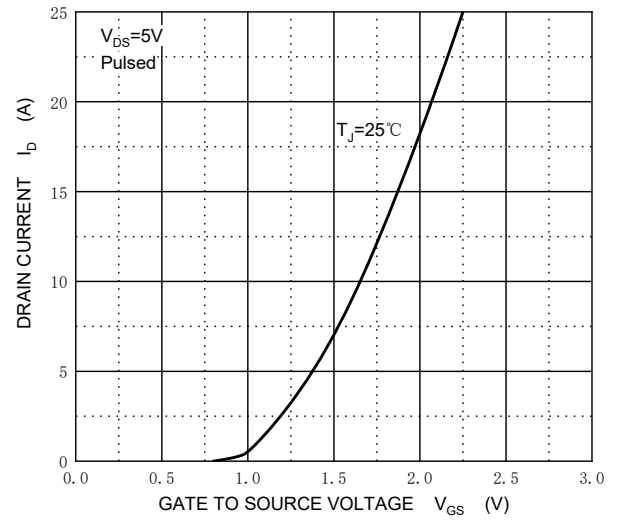
Notes:

- 1.Repetitive Rating : Pulse width limited by maximum junction temperature.
- 2.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 3.Guaranteed by design, not subject to production testing.

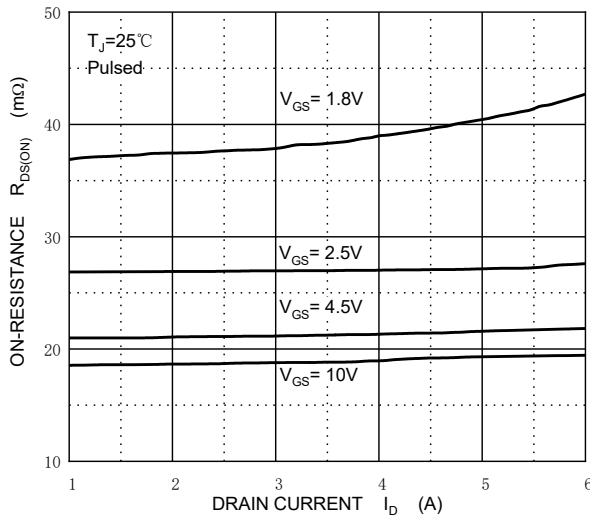
Output Characteristics



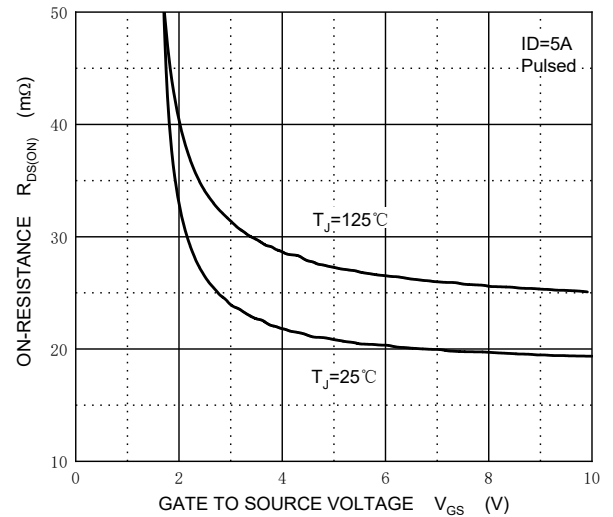
Transfer Characteristics



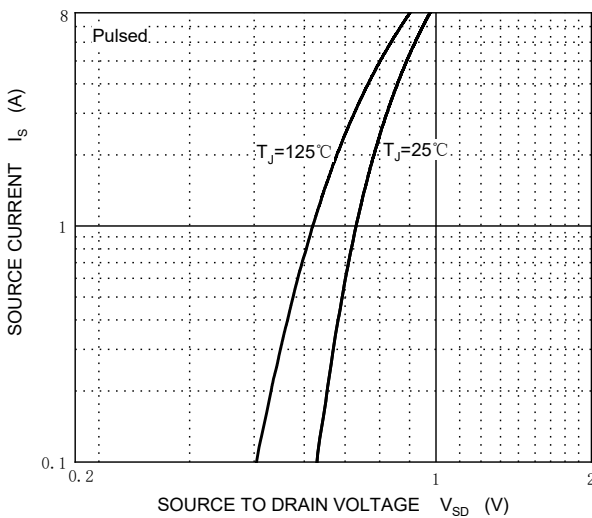
$R_{DS(ON)}$ — I_D



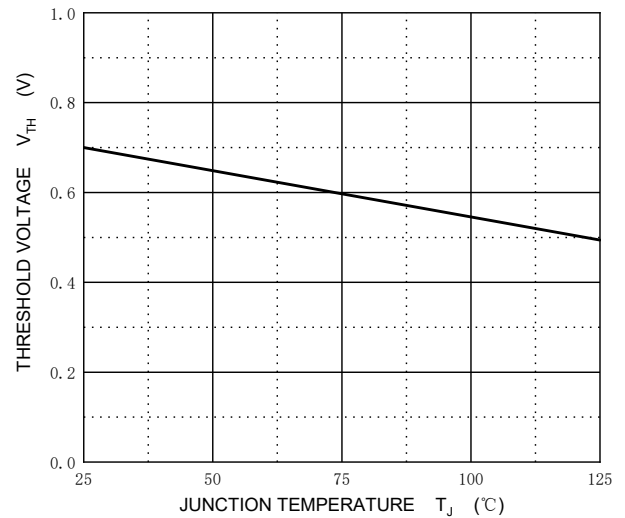
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}



Threshold Voltage





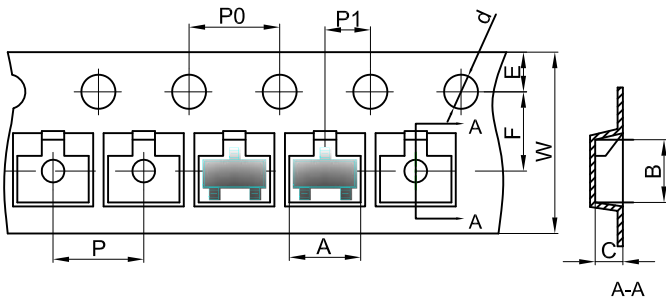
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



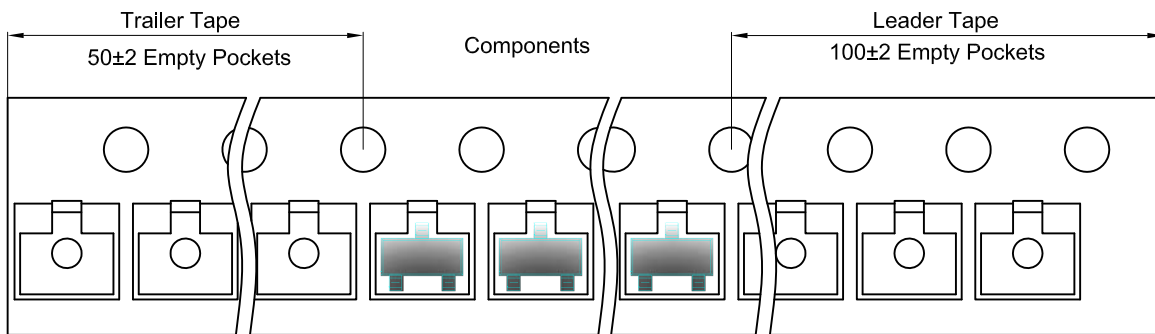
- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

SOT-23 Embossed Carrier Tape

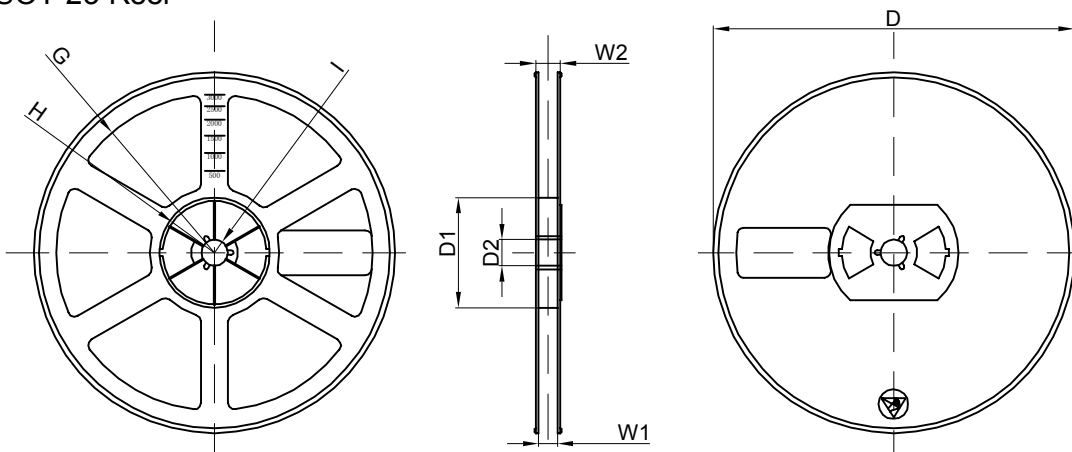


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box
3000 pcs	7 inch	3000 pcs